YUYUE

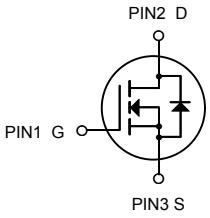
7N50

N-Channel Enhancement Mode MOSFET

Â DESCRIPTION

The **7N50** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The **7N50** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.



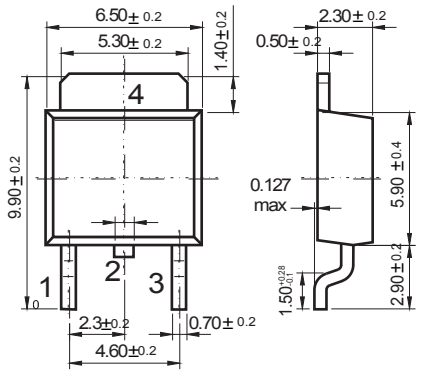
General Features

V_{DS} = 500V ID = 7A

$R_{DS(ON)}$ 0.85Ω

TO-252

Unit: mm



Dimensions in inches and (millimeters)

Â ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	500	V
Gate-Source Voltage			V_{GSS}	±30	V
Drain Current	Continuous (T_C=25°C)		I_D	7 *	A
	Pulsed (Note 1)		I_{DM}	28 *	A
Avalanche Current (Note 1)			I_{AR}	7	A
Avalanche Energy	Single Pulsed (Note 2)		E_{AS}	270	mJ
	Repetitive (Note 3)		E_{AR}	8.9	mJ
Peak Diode Recovery dv/dt (Note 3)			dv/dt	4.5	V/ns
Power Dissipation	T_C=25°C	TO-220	P_D	89	W
		TO-220F1		39	
	Derate above 25°C	TO-220		0.71	W/°C
		TO-220F1		0.31	
Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

* Drain current limited by maximum junction temperature

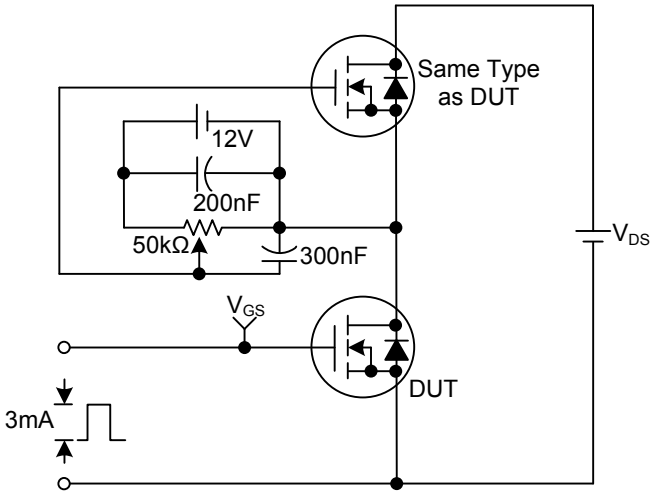
Â ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	500			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=500V, V_{GS}=0V			1	μA
			V_{DS}=400V, T_C=125°C			10	
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=3.5A		0.85	1.05	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		720	940	pF
Output Capacitance		C_{OSS}			95	190	pF
Reverse Transfer Capacitance		C_{RSS}			9	13.5	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DS}=400V, I_D=7A (Note 4, 5)		12.8	16.6	nC
Gate to Source Charge		Q_{GS}			3.7		nC
Gate to Drain Charge		Q_{GD}			5.8		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=250V, I_D=7A, R_G=25Ω (Note 4, 5)		6	20	ns
Rise Time		t_R			55	120	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			25	60	ns
Fall-Time		t_F			35	80	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				7	A
Maximum Body-Diode Pulsed Current		I_{SM}				28	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=7A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{RR}	I_S=7A, V_{GS}=0V, dI_F/dt=100A/μs (Note 4)		275		ns
Body Diode Reverse Recovery Charge		Q_{RR}			0.04		μC

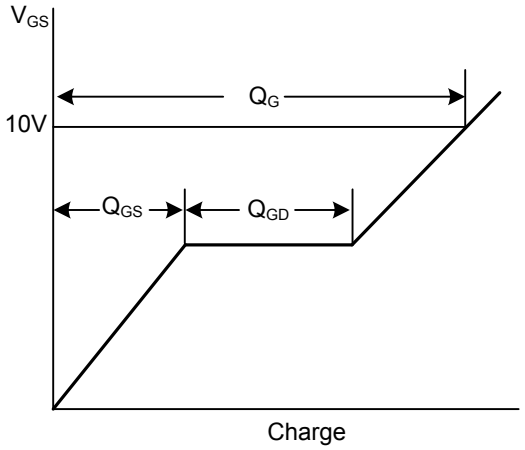
Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 10mH, I_{AS} = 7A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 7A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

RATING AND CHARACTERISTIC CURVES (7N50)

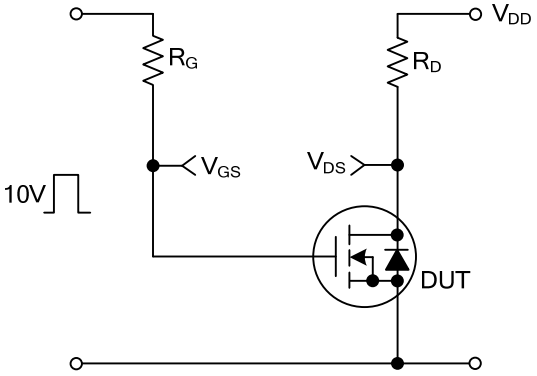
Gate Charge Test Circuit



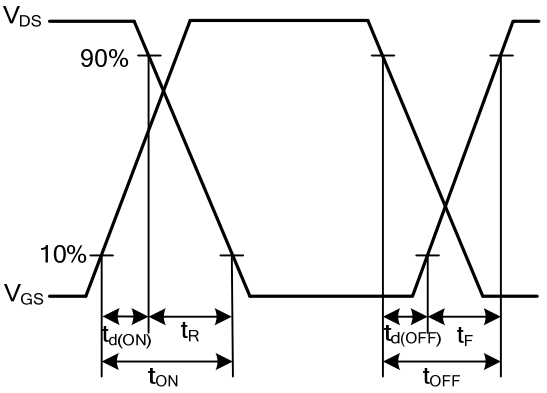
Gate Charge Waveforms



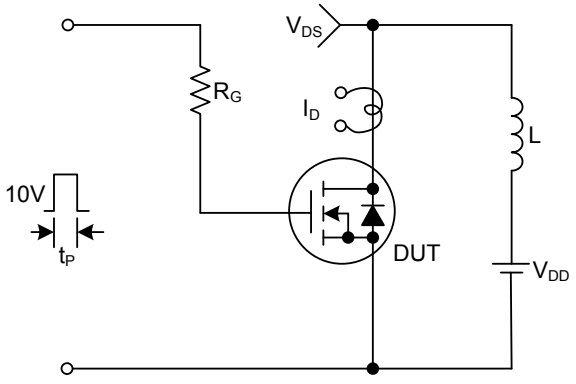
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

$$E_{AS}=\frac{1}{2}LI_{AS}^{2}\frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$